Dual N-Channel 70-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

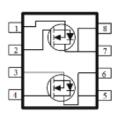
PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
70	32 @ V _{GS} = 10V	24	
	$38 @ V_{GS} = 4.5V$	22	







DFN3x3-8L



Top View

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Limit	Units			
Drain-Source Voltage			70	V		
Gate-Source Voltage			±20	V		
	T _C =25°C	I _D	24	A		
Continuous Drain Current	T _C =70°C		19			
Continuous Brain Guirent	T _A =25°C		5.6 ^a			
	T _A =70°C		4.6 ^a	^		
Pulsed Drain Current ^b	I _{DM}	25				
Continuous Source Current (Diode Conduction) a	I _S	2.5				
	T _C =25°C		28	W		
Power Dissipation	T _C =70°C	P_{D}	18			
r ower dissipation	T _A =25°C] ' Þ	1.5 ^a			
	T _A =70°C		1 ^a			
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	D	83	°C/W			
IMAXIMUM JUNCTION-TO-AMBIENT	Steady State	$R_{\theta JA}$	120				
Maximum Junction-to-Case	Steady State	$R_{\theta JC}$	4.5				

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

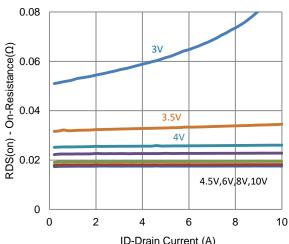
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zara Cata Valta za Brain Commant		$V_{DS} = 56 \text{ V}, V_{GS} = 0 \text{ V}$		1		uA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 56 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α	
Dania Carras On Basistana a	r	$V_{GS} = 10 \text{ V}, I_{D} = 3 \text{ A}$	3		32	0	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 2.5 \text{ A}$			38	mΩ	
Forward Transconductance a	g_{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 3 \text{ A}$		25		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 1.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.73		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 30 \text{ V}, V_{GS} = 4.5 \text{ V},$		24			
Gate-Source Charge	Q_{gs}	$I_D = 3 A$		3.9		nC	
Gate-Drain Charge	Q_gd	1B = 3 K		3.5			
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 30 \text{ V}, R_{L} = 10 \Omega,$		5			
Rise Time	t _r	$V_{DS} = 30 \text{ V}, R_L - 10 \Omega,$ $I_D = 3 \text{ A},$		5		nc	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		36		ns	
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.12		11			
Input Capacitance	C _{iss}			1597			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		92		рF	
Reverse Transfer Capacitance	C _{rss}			99			

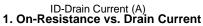
Notes

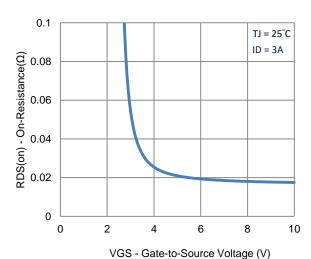
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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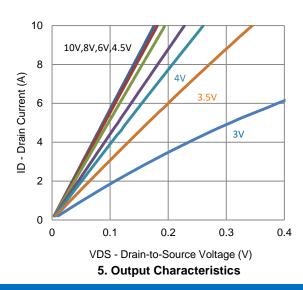
Typical Electrical Characteristics

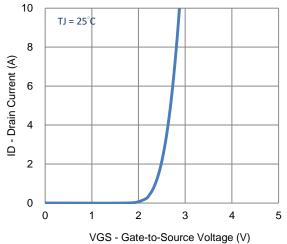




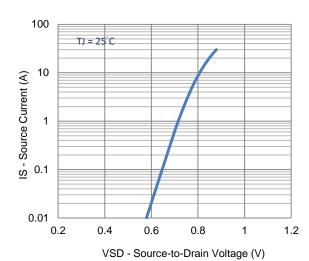


3. On-Resistance vs. Gate-to-Source Voltage

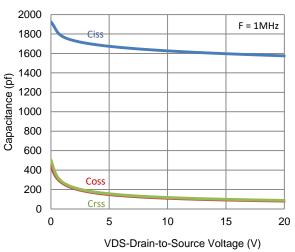




2. Transfer Characteristics



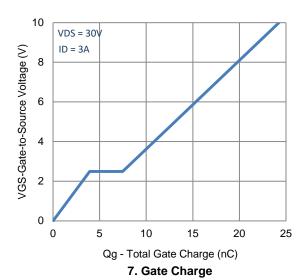
4. Drain-to-Source Forward Voltage

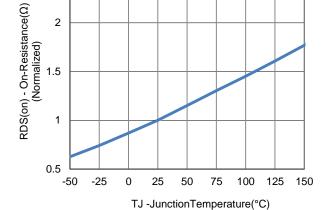


6. Capacitance

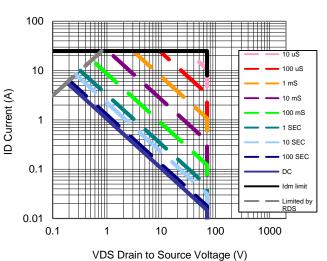
Typical Electrical Characteristics

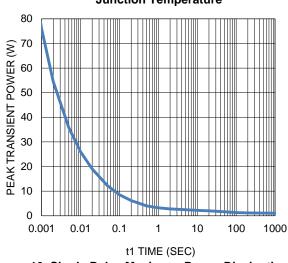
2.5





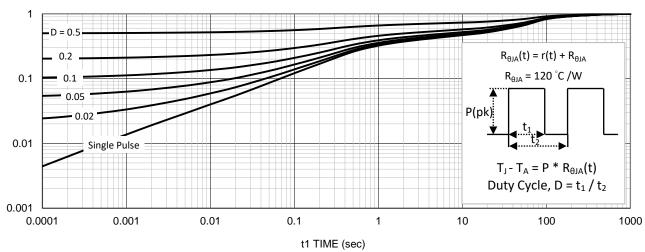
8. Normalized On-Resistance Vs Junction Temperature





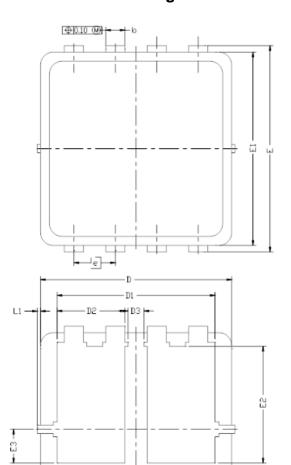
9. Safe Operating Area

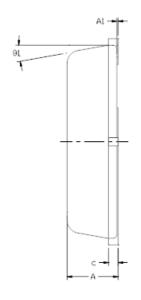
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information





DIM.	MILLIMETERS			INCHES			
DIM	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.70	0.80	0.90	0.0276	0.0315	0.0354	
A1	0.00		0.05	0.000		0.002	
b	0.24	0.30	0.35	0.009	0.012	0.014	
C	0.10	0.152	0.25	0.004	0.006	0.010	
D	3.00 BSC			0.118 BSC			
D1	2.475 BSC			0.093 BSC			
D2	1.063 BSC			0.042 BSC			
DЗ	0.	0.225 BSC			0.009 BSC		
Е	3.20 BSC			0.126 BSC			
E1	3.00 BSC			0.118 BSC			
E2	1.813 BSC			0.069 BSC			
E3	0.525 BSC			0.023 BSC			
6	0.65 BSC			0.026 BSC			
L	0.30	0.40	0.50	0.0118	0.0157	0.0197	
L1	0		0.100	0		0.004	
-	0?	10?	12?	0?	10?	12?	